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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Leonard Forbes et al.

Title: GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION

Docket No.: 1303.108US1

Serial No.: 10/623,794

Filed: July 21, 2003

Due Date: July 10, 2004

Examiner: Fazli Erdem

Group Art Unit: 2826

Mail Stop Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ Response to Restriction Requirement (1 Page).
- ☒ A Communication Concerning Related Applications (3 pgs.).

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number 21186

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 7th day of July, 2004.

Name

Amy Moriarty

Signature

[Signature]

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(GENERAL)



S/N 10/623,794

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Fazli Erdem
Serial No.: 10/623,794 Group Art Unit: 2826
Filed: July 21, 2003 Docket: 1303.108US1
Title: GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

| <u>Serial/Patent No.</u> | <u>Filing Date</u> | <u>Attorney Docket</u> | <u>Title</u> |
|--------------------------|--------------------|------------------------|---|
| 10/052952 | January 17, 2002 | 1303.034US1 | THREE-DIMENSIONAL PHOTONIC CRYSTAL WAVEGUIDE STRUCTURE AND METHOD |
| 10/382246 | March 5, 2003 | 1303.086US1 | CELLULAR MATERIALS FORMED USING SURFACE TRANSFORMATION |
| 10/379749 | March 5, 2003 | 1303.089US1 | MICRO-MECHANICALLY STRAINED SEMICONDUCTOR FILM |
| 10/425797 | April 29, 2003 | 1303.093US1 | LOCALIZED STRAINED SEMICONDUCTOR ON INSULATOR |
| 10/431134 | May 7, 2003 | 1303.094US1 | STRAINED Si/SiGe STRUCTURES BY ION IMPLANTATION |
| 10/425484 | April 29, 2003 | 1303.095US1 | STRAINED SEMICONDUCTOR BY WAFER BONDING WITH MISORIENTATION |
| 10/443355 | May 21, 2003 | 1303.098US1 | SILICON OXYCARBIDE SUBSTRATES FOR BONDED SILICON ON INSULATOR |

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/623,794

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|----------------------|----------------------|-------------|--|
| 10/443340 | May 21, 2003 | 1303.099US1 | ULTRA-THIN SEMICONDUCTORS BONDED ON GLASS SUBSTRATES |
| 10/431137 | May 7, 2003 | 1303.100US1 | MICROMECHANICAL STRAINED SEMICONDUCTOR BY WAFER BONDING |
| 10/634174 | August 5, 2003 | 1303.102US1 | STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME |
| 10/443337 | May 21, 2003 | 1303.103US1 | GETTERING OF SILICON ON INSULATOR USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS |
| 10/443339 | May 21, 2003 | 1303.104US1 | WAFER GETTERING USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS |
| 10/623788 | July 21, 2003 | 1303.109US1 | STRAINED SEMICONDUCTOR BY FULL WAFER BONDING |
| 09/855532 | May 16, 2001 | | METHOD OF FORMING MIRRORS BY SURFACE TRANSFORMATION OF EMPTY SPACES IN SOLID STATE MATERIALS |
| 09/861770 6582512 | May 22, 2001 | | METHOD OF FORMING THREE- DIMENSIONAL PHOTONIC BAND STRUCTURES IN SOLID MATERIALS |
| 09/734547 6383924 | December 13, 2000 | | METHOD OF FORMING BURIED CONDUCTOR PATTERNS BY SURFACE TRANSFORMATION OF EMPTY SPACES IN SOLID STATE MATERIALS |
| 10/118350 | April 9, 2002 | | METHOD OF FORMING SPATIAL REGIONS OF A SECOND MATERIAL IN A FIRST MATERIAL |
| 10/093332 | March 7, 2002 | | METHOD AND APPARATUS FOR PACKAGING SEMICONDUCTOR DEVICES |



COMMUNICATION CONCERNING RELATED APPLICATIONS

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Respectfully submitted,

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